

**SEMIPONT™ 6**

## 3-Phase Bridge Rectifier + IGBT braking chopper

**SKD116/18-L75**

### Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

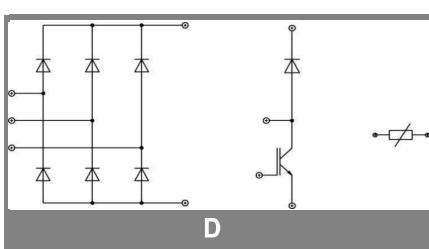
### Typical Applications\*

- DC drives
- Controlled field rectifiers for DC motors
- Controlled battery charger

$V_{RSM}$ V 1900	$V_{RRM}, V_{DRM}$ V 1800	$I_D = 110 \text{ A}$ (maximum value for continuous operation) $(T_s = 85^\circ \text{C})$ SKD 116/18-L75
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<b>Absolute Maximum Ratings</b>		$T_s = 25^\circ \text{C}$ , unless otherwise specified	
<b>Symbol</b>	<b>Conditions</b>	<b>Values</b>	<b>Units</b>
<b>Bridge - Rectifier</b>			
$I_D$	$T_s = 85^\circ \text{C}$ ; inductive load	110	A
$I_{FSM}/I_{TSM}$	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	1050	A
$i^2t$	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	5500	A <sup>2</sup> s
<b>IGBT - Chopper</b>			
$V_{CES}/V_{GES}$		1200 / 20	V
$I_C$	$T_s = 25 (70)^\circ \text{C}$	100 (75)	A
$I_{CM}$	$t_p = 1 \text{ ms}; T_s = 25 (70)^\circ \text{C}$	200 (150)	A
<b>Freewheeling - CAL Diode</b>			
$V_{RRM}$		1200	V
$I_F$	$T_s = 25 (70)^\circ \text{C}$	90 (70)	A
$I_{FM}$	$t_p = 1 \text{ ms}; T_s = 25 (70)^\circ \text{C}$	180 (140)	A
$T_{vj}$	Diode & IGBT (Thyristor)	- 40 ... + 150 (-40...+ 125)	°C
$T_{stg}$		- 40 ... + 125	°C
$T_{solder}$	terminals, 10 s	260	°C
$V_{isol}$	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V

<b>Characteristics</b>		$T_s = 25^\circ \text{C}$ , unless otherwise specified		
<b>Symbol</b>	<b>Conditions</b>	<b>min.</b>	<b>typ.</b>	<b>max.</b>
<b>Diode - Rectifier</b>				
$V_{TO} / r_t$	$T_j = 125^\circ \text{C}$	0,8 / 7		V / mΩ
$R_{th(j-s)}$	per diode		1	K/W
<b>IGBT - Chopper</b>				
$V_{CE(sat)}$	$I_C = 75 \text{ A}; T_j = 25^\circ \text{C}; V_{GE} = 15 \text{ V}$	2,35		V
$R_{th(j-s)}$	per IGBT		0,4	K/W
$t_{d(on)} / t_r$	valid for all values:			
$t_{d(off)} / t_r$	$V_{CC} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 90 \text{ A}; T_j = 125^\circ \text{C};$	113,8 / 94,4		ns
$E_{on} + E_{off}$	$T_j = 125^\circ \text{C}; R_G = 16 \Omega$ ; inductive load	845,4 / 94,4		ns
		18,3		mJ
<b>CAL - Diode - Freewheeling</b>				
$V_{T(TO)} / r_t$	$T_j = 125^\circ \text{C}$	1 / 8	1,2 / 11	V / mΩ
$R_{th(j-s)}$	per diode		0,8	K/W
$I_{RRM}$	valid for all values:	65		A
$Q_{rr}$	$I_F = 100 \text{ A}; V_R = -600 \text{ V}; dI_F/dt = -1000 \text{ A}/\mu\text{s}$	15		μC
$E_{off}$	$V_{GE} = 0 \text{ V}; T_j = 125^\circ \text{C}$			mJ
<b>Temperature Sensor</b>				
$R_{TS}$	$T = 25 (100)^\circ \text{C}$	1000 (1670)		Ω
<b>Mechanical data</b>				
$M_S$	mounting Torque	2,55	3,45	Nm



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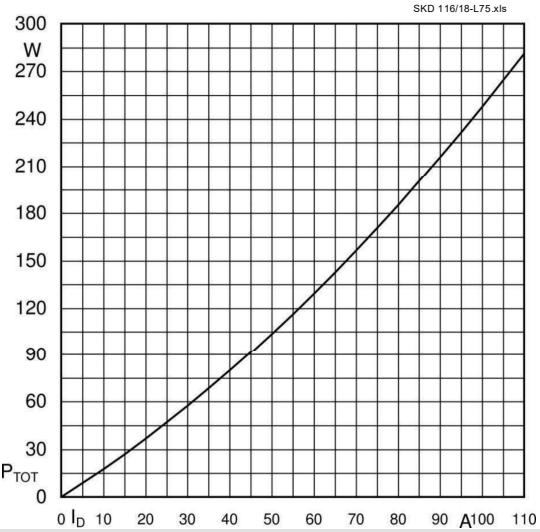


Fig. 1 Power dissipation per module vs. output current

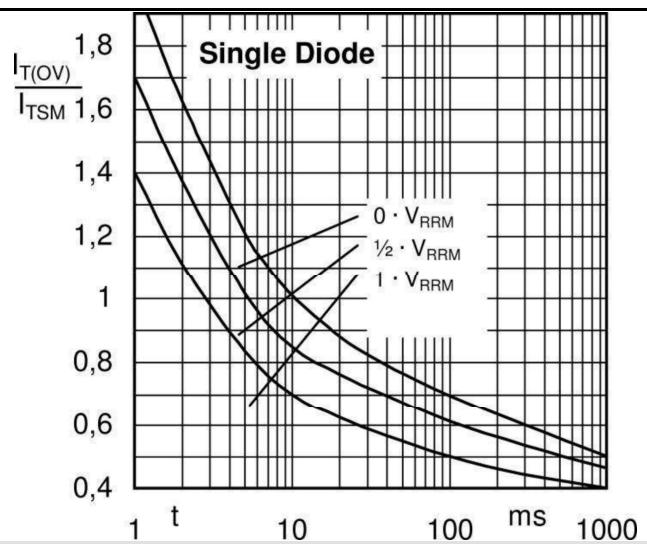


Fig. 2 Surge overload current vs. time

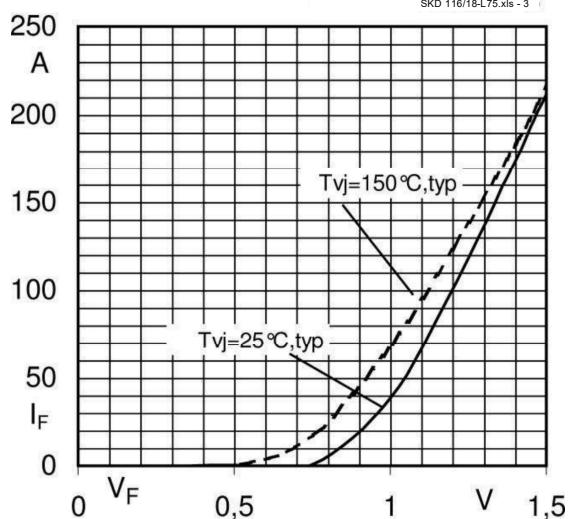


Fig. 3 Forward characteristic of single rectifier diode

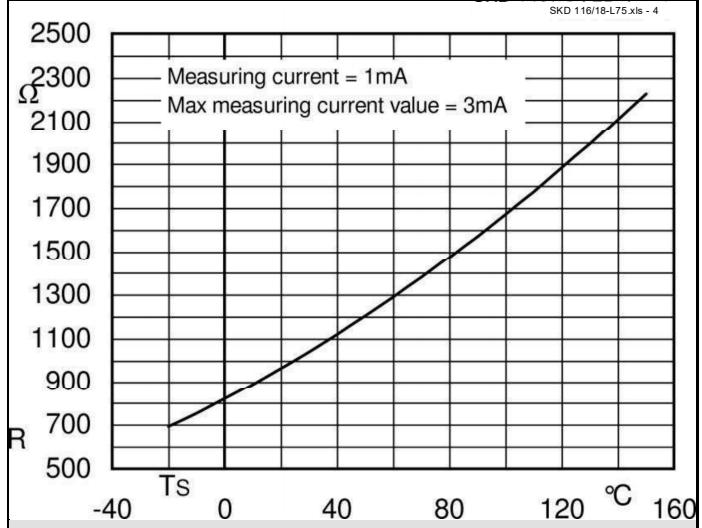


Fig. 4 Temperature sensor characteristic

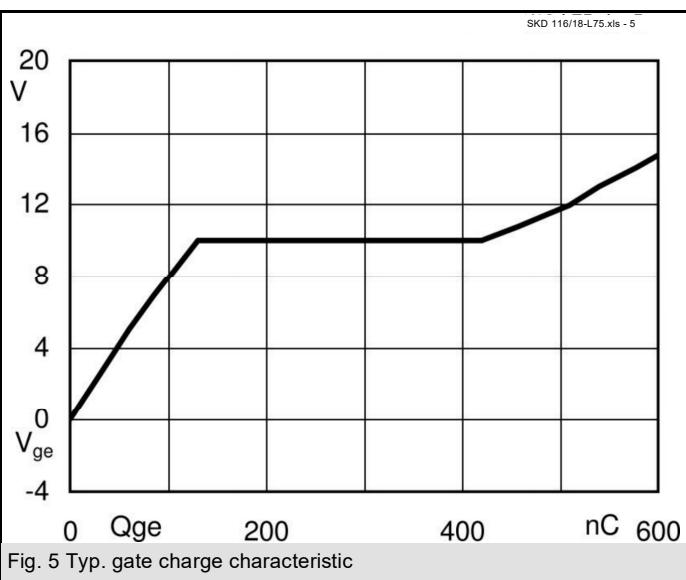


Fig. 5 Typ. gate charge characteristic

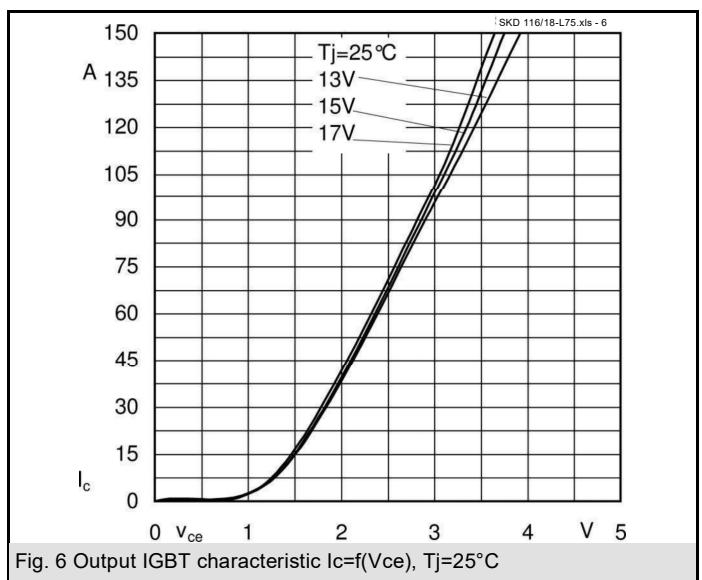


Fig. 6 Output IGBT characteristic  $I_c=f(v_{ce})$ ,  $T_j=25^{\circ}\text{C}$

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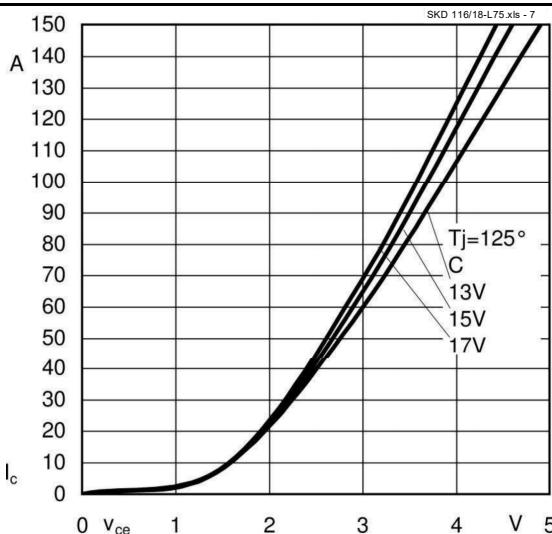


Fig. 7 Output IGBT characteristic  $I_c=f(V_{ce})$ ,  $T_j=125^\circ\text{C}$

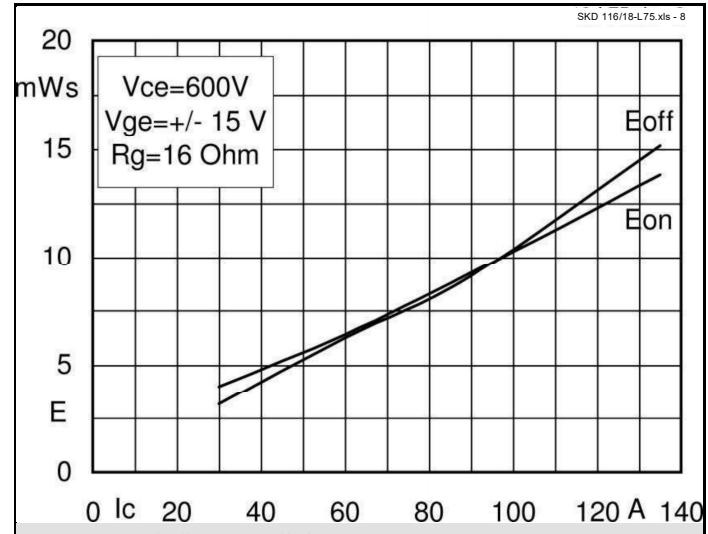


Fig. 8 Turn-on/-off energy  $=f(I_c)$

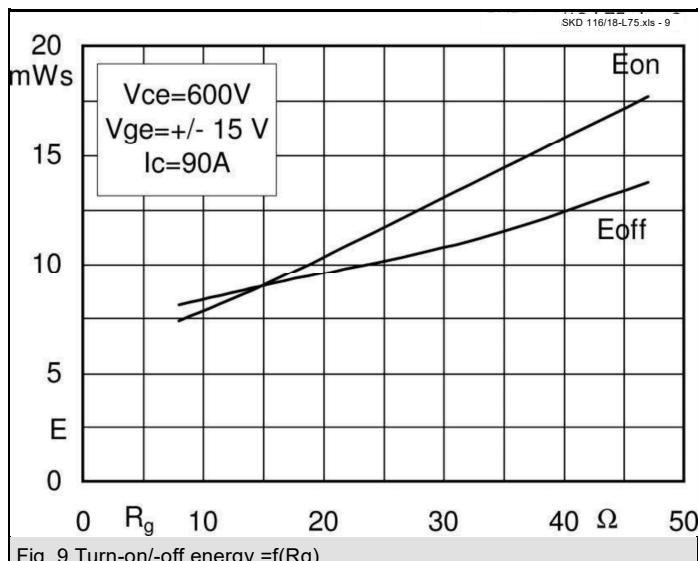


Fig. 9 Turn-on/-off energy  $=f(R_g)$

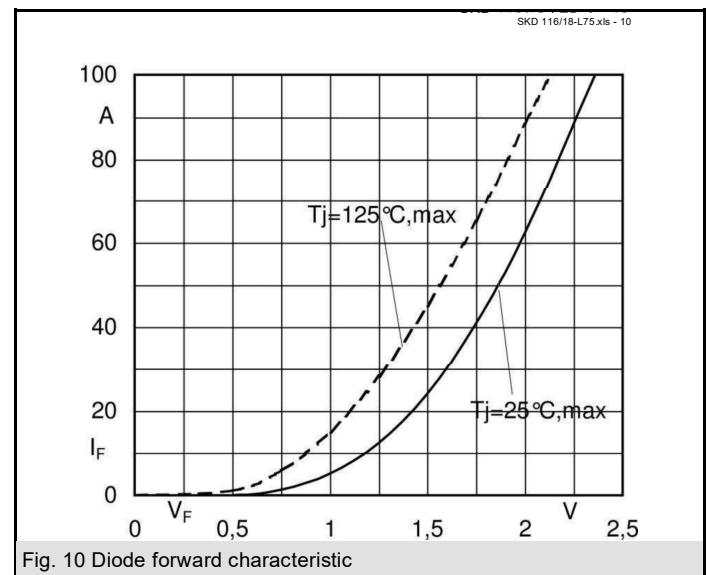
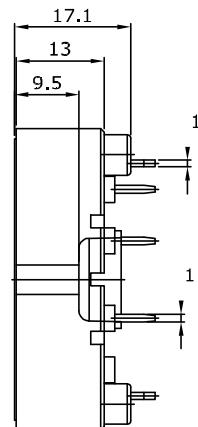
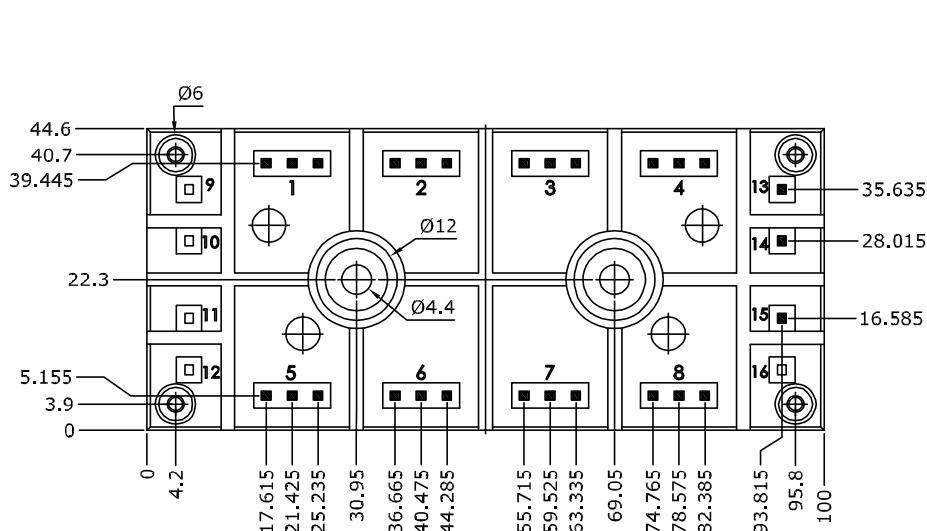
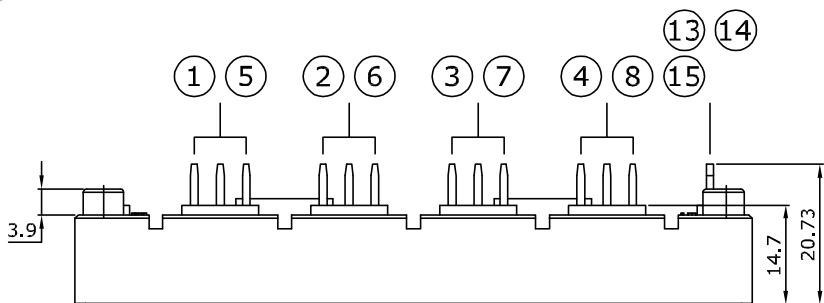


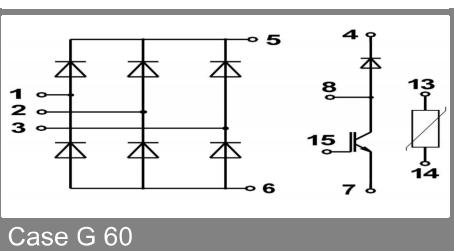
Fig. 10 Diode forward characteristic

UL recognized  
File no. E 63 532

Dimensions in mm



Case G 60



Case G 60

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

## \*IMPORTANT INFORMATION AND WARNINGS

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